

Description

The HSBB3105 is the high cell density trench P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

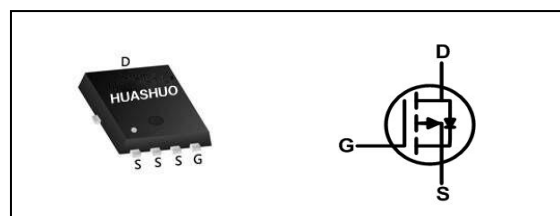
The HSBB3105 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V_{DS}	-30	V
$R_{DS(ON),max}$	14	mΩ
I_D	-42	A

PRPAK3X3 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		10s	Steady State	
V_{DS}	Drain-Source Voltage	-30		V
V_{GS}	Gate-Source Voltage	± 20		V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-42		A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-27		A
$I_D@T_A=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-14.3	-9	A
$I_D@T_A=70^{\circ}C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-11.4	-7.2	A
I_{DM}	Pulsed Drain Current ²	-130		A
EAS	Single Pulse Avalanche Energy ³	125		mJ
I_{AS}	Avalanche Current	-37		A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ⁴	37		W
$P_D@T_A=25^{\circ}C$	Total Power Dissipation ⁴	4.2	1.67	W
T_{STG}	Storage Temperature Range	-55 to 150		$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150		$^{\circ}C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	75	$^{\circ}C/W$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ (t ≤ 10s)	---	30	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	3.36	$^{\circ}C/W$

Electrical Characteristics ($T_J=25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V$, $I_D=-30A$	---	11	14	$m\Omega$
		$V_{GS}=-4.5V$, $I_D=-15A$	---	15	18	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-1.0	-1.5	-2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-24V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	-1	μA
		$V_{DS}=-24V$, $V_{GS}=0V$, $T_J=55^{\circ}\text{C}$	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V$, $I_D=-30A$	---	30	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	9	---	Ω
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-15V$, $V_{GS}=-4.5V$, $I_D=-15A$	---	22	---	nC
Q_{gs}	Gate-Source Charge		---	8.7	---	
Q_{gd}	Gate-Drain Charge		---	7.2	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-15V$, $V_{GS}=-10V$, $R_G=3.3\Omega$ $I_D=-15A$	---	8	---	ns
T_r	Rise Time		---	73.7	---	
$T_{d(off)}$	Turn-Off Delay Time		---	61.8	---	
T_f	Fall Time		---	24.4	---	
C_{iss}	Input Capacitance	$V_{DS}=-15V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	2215	---	pF
C_{oss}	Output Capacitance		---	310	---	
C_{rss}	Reverse Transfer Capacitance		---	237	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	-25	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=-1A$, $T_J=25^{\circ}\text{C}$	---	---	-1	V
t_{rr}	Reverse Recovery Time	$I_F=-15A$, $dI/dt=100A/\mu s$, $T_J=25^{\circ}\text{C}$	---	19	---	nS
Q_{rr}	Reverse Recovery Charge		---	9	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=-25V$, $V_{GS}=-10V$, $L=0.1mH$, $I_{AS}=-37A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

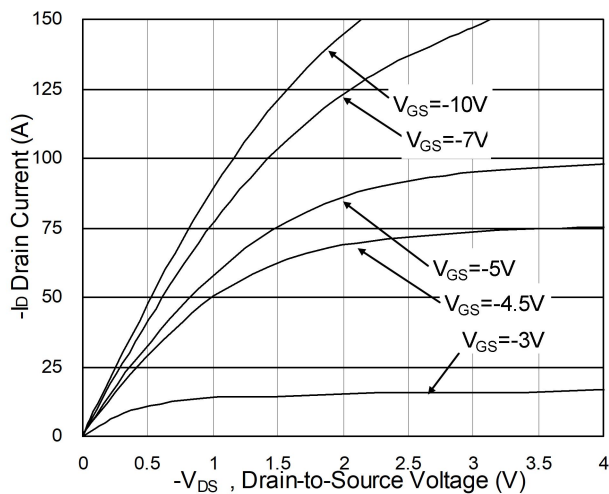


Fig.1 Typical Output Characteristics

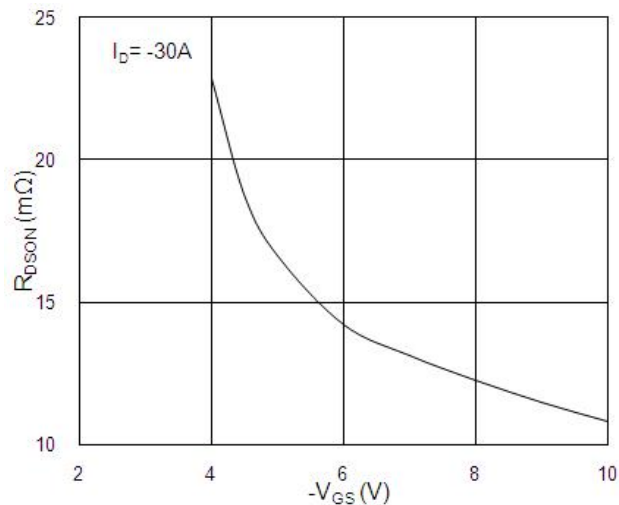


Fig.2 On-Resistance vs. G-S Voltage

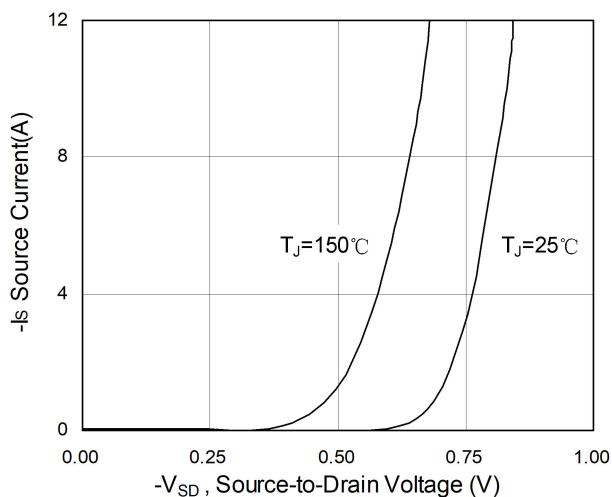


Fig.3 Source Drain Forward Characteristics

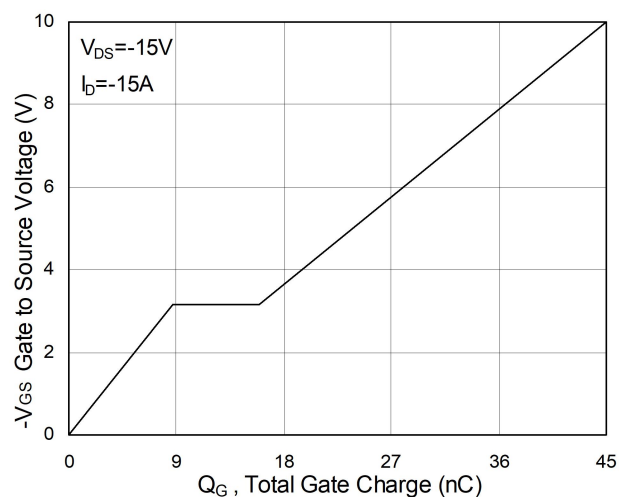


Fig.4 Gate-Charge Characteristics

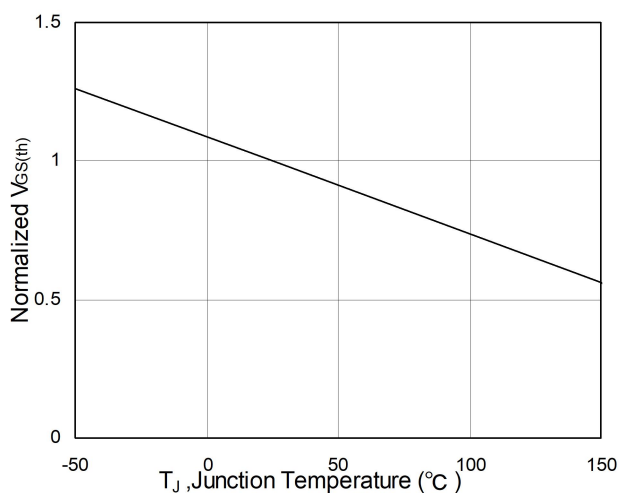


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

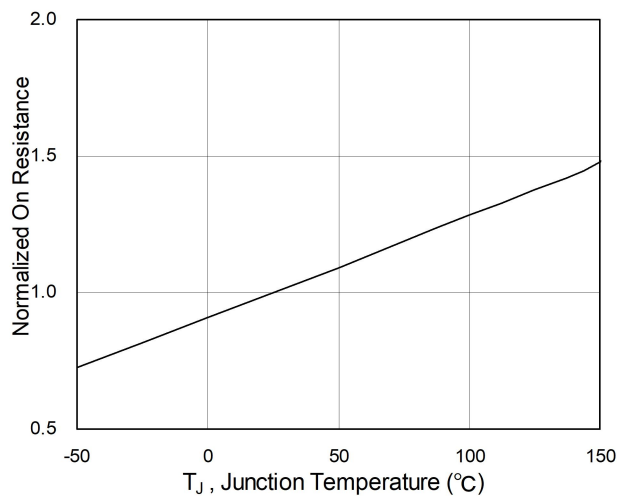


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

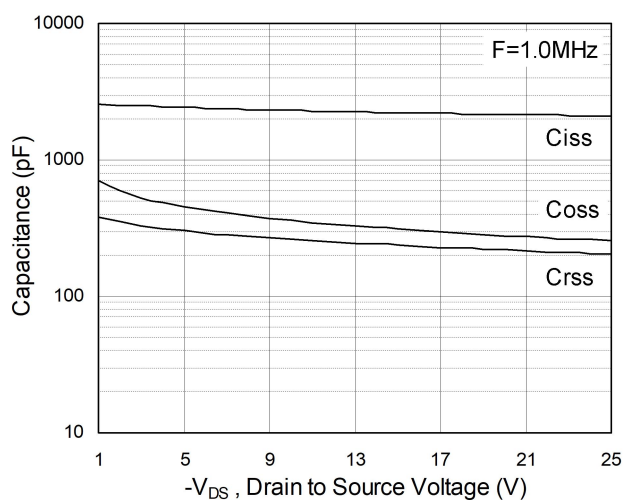


Fig.7 Capacitance

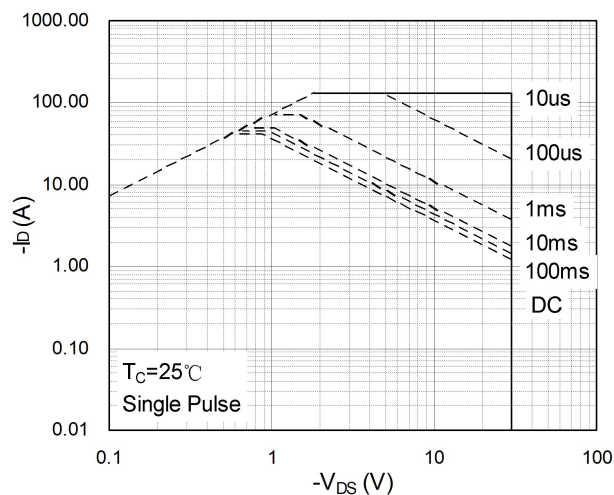


Fig.8 Safe Operating Area

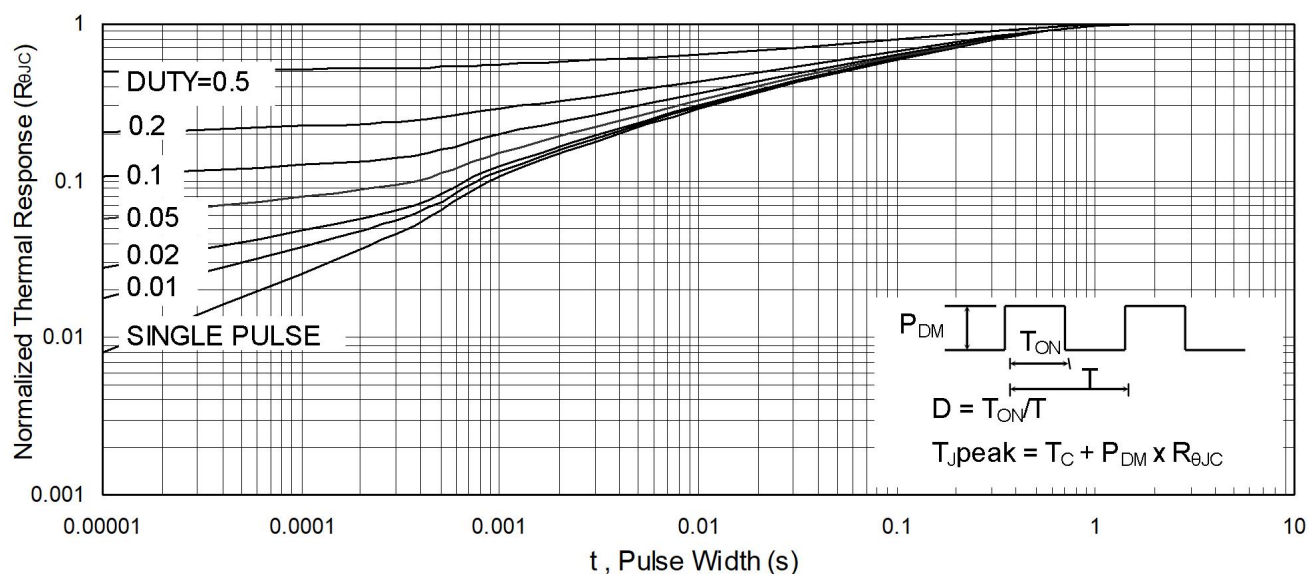


Fig.9 Normalized Maximum Transient Thermal Impedance

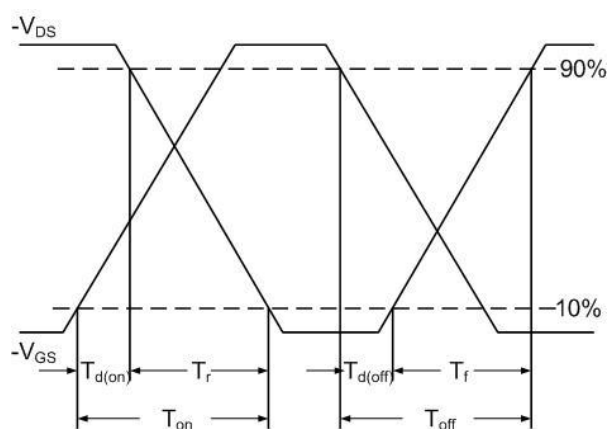


Fig.10 Switching Time Waveform

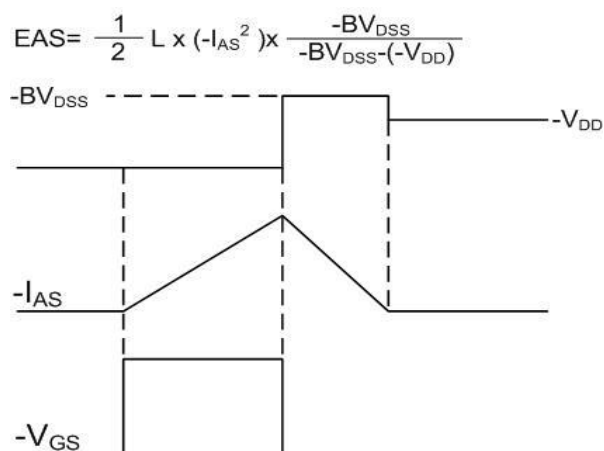
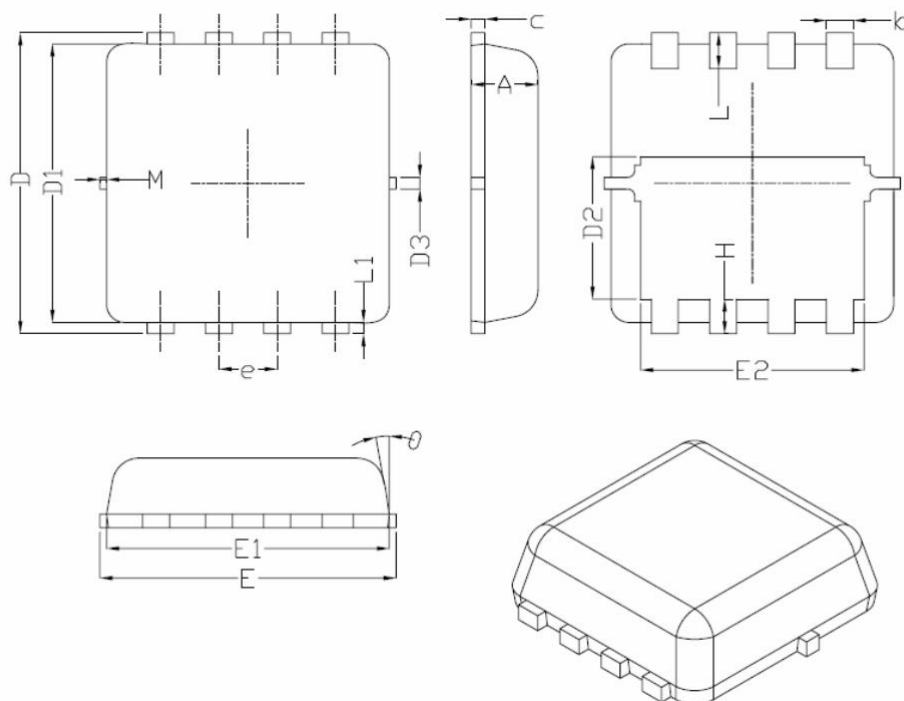


Fig.11 Unclamped Inductive Switching Waveform

Ordering Information

Part Number	Package code	Packaging
HSBB3105	PRPAK3*3	3000/Tape&Reel



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.15	3.30	3.45
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°